

GSTSS8050

NPN General Purpose Transistor

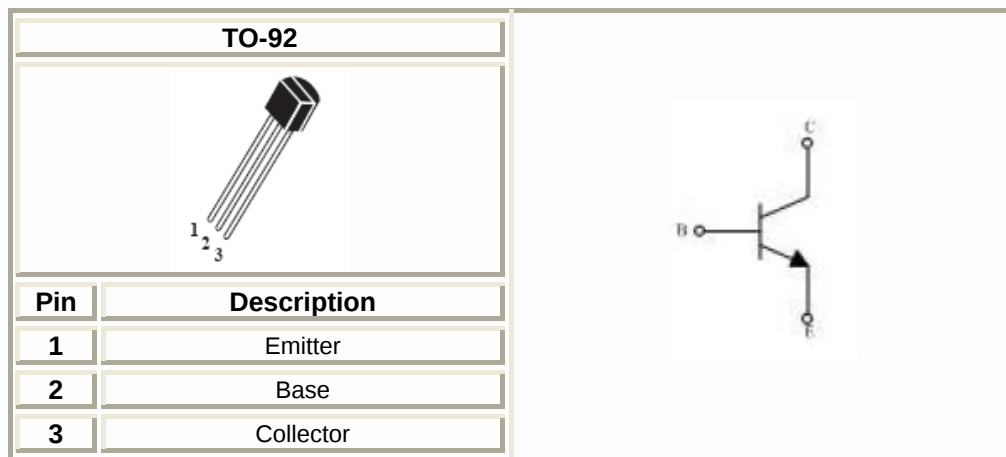
Product Description

This device is designed as a general purpose amplifier and switch.

Features

- Collector-Emitter Voltage : 25V
- Collector Current : 1.5A
- Lead(Pb)-Free

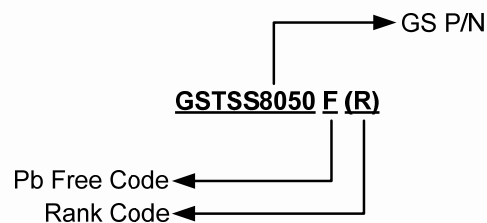
Packages & Pin Assignments



Marking Information

P/N	Package	Rank	Part Marking
GSTSS8050F	TO-92	(B) / (C) / (D) / (E)	SS8050

Ordering Information



Part Number	Package	Quantity
GSTSS8050F(B or C or D or E)	TO-92	1000 PCS

Absolute Maximum Ratings

(T_A=25°C unless otherwise noted)

Symbol	Conditions	Typical	Unit
V _{CEO}	Collector-Emitter Voltage	25	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5	V
I _{C(DC)}	Collector Current (DC)	1.5	A
P _D	Total Device Dissipation T _A =25°C	1.0	W
T _J	Junction Temperature Range	-55 to +150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

Electrical Characteristics

(T_A=25°C unless otherwise noted)

Symbol	Conditions	Min	TYP	Max	Unit
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage (I _C =0.1mA, I _B =0mA)	25	-	-	V
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _C =100uA, I _E =0mA)	40	-	-	V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _E =100uA, I _C =0mA)	5	-	-	V
I _{CEO}	Collector-Emitter Cutoff Current (V _{CE} =20V, I _B =0mA)	-	-	0.1	uA
I _{CBO}	Collector-Base Cutoff Current (V _{CB} =40V, I _E =0mA)	-	-	0.1	uA
I _{EBO}	Emitter-Base Cutoff Current (V _{EB} =5V, I _C =0mA)	-	-	0.1	uA
h _{FE (1)}	DC Current Gain (I _C =100mA, V _{CE} =1V)	85	-	400	-
h _{FE (2)}	DC Current Gain (I _C =800mA, V _{CE} =1V)	40	-	-	-
V _{CE(sat)}	Collector-Emitter Saturation Voltage (I _C =800mA, I _B =80mA)	-	-	0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage (I _C =800mA, I _B =80mA)	-	-	1.2	V
V _{BE(ON)}	Base-Emitter ON Voltage (I _C =10mA, V _{CE} =1V)	-	-	1	V
f _T	Transition Frequency (I _C =50mA, V _{CE} =10V, f=30MHz)	100	-	-	MHz

Classification of h_{FE(1)}

Rank	B	C	D	E
Range	85-160	120-200	160-300	300-400

Typical Performance Characteristics

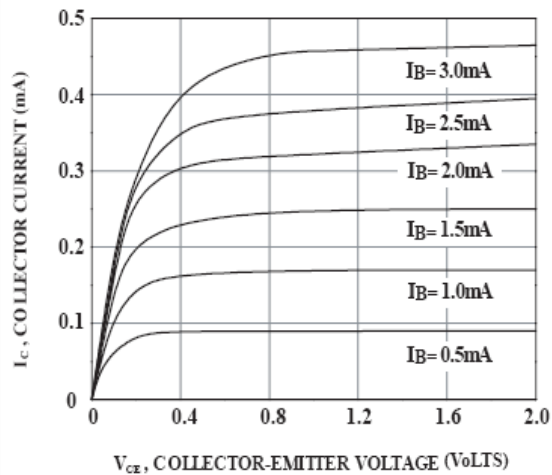


FIG.1 Static Characteristic

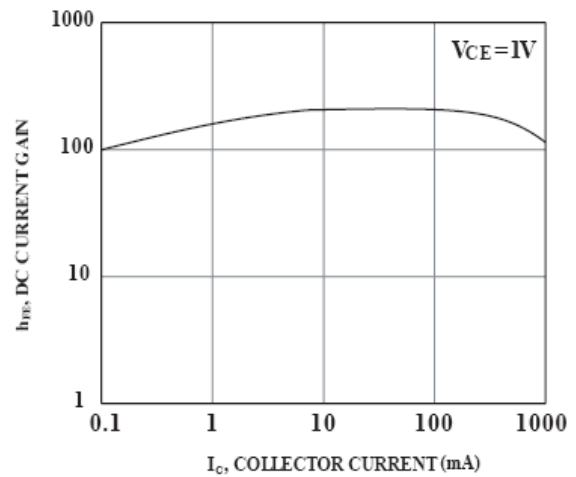


FIG.2 DC Current Gain

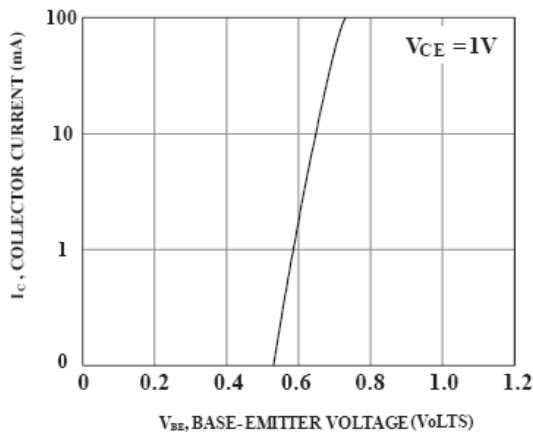


FIG.3 Base-Emitter On Voltage

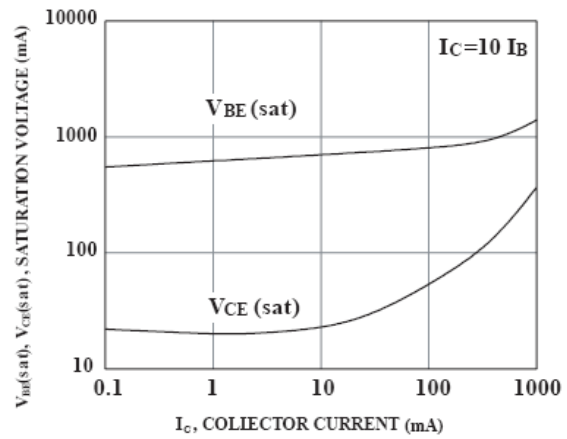


FIG.4 Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

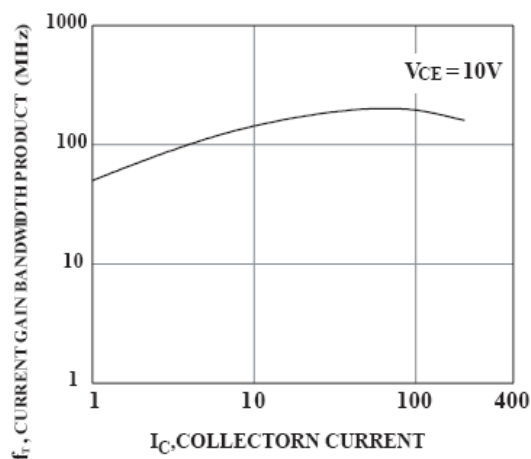


FIG.5 Current Gain Bandwidth Product

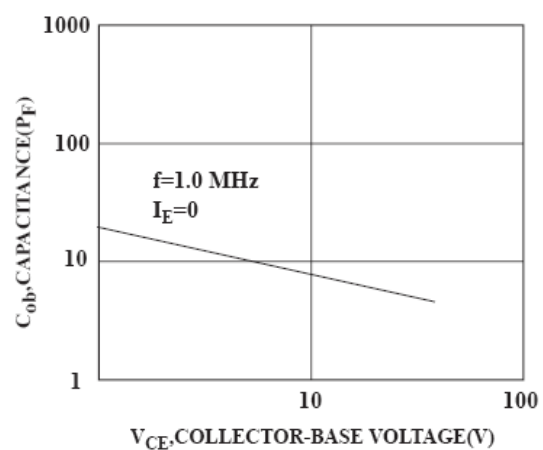
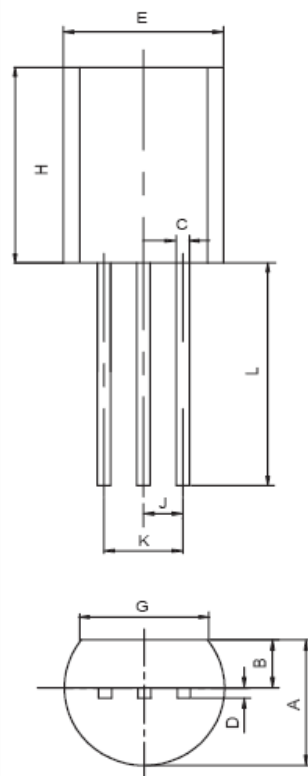


FIG.6 Collector Output Capacitance

Package Dimension

TO-92



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	3.30	3.70	0.13	0.15
B	1.10	1.40	0.04	0.06
C	0.38	0.55	0.015	0.022
D	0.36	0.51	0.014	0.020
E	4.40	4.70	0.173	0.185
G	3.43	-	0.135	-
H	4.30	4.70	0.169	0.185
J	1.270(TYP)		0.050(TYP)	
K	2.44	2.64	0.096	0.104
L	14.10	14.50	0.555	0.571

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